L Number	Hits	Search Text	DB	Time stamp
-	83	laser same anneal\$3 same (silicon or si) and 117/904.ccls.	USPAT; US-PGPUB; EPO; JPO;	2002/09/05 15:58
_	1.2	laser same anneal\$3 same (silicon or si)	DERWENT; IBM_TDB	
	1	and 117/\$4.ccls. and (CVD or chemical adjuapor adj deposition) same plasma and ion near3 beam	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/05
_	78	laser same anneal\$3 same (silicon or si) and 117/\$4.ccls. and (CVD or chemical adj	IBM_TDB USPAT; US-PGPUB;	2002/09/05
	,	vapor adj deposition) same plasma same (si or silicon)	EPO; JPO; DERWENT; IBM TDB	
	41	laser same anneal\$3 same (silicon or si) and 117/\$4.ccls. and (CVD or chemical adj vapor adj deposition) same plasma same (si or silicon) and apparatus	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/05
-	15	laser same (kev) same anneal\$3 and 117/\$4.ccls.	<pre>IBM_TDB USPAT; US-PGPUB;</pre>	2002/09/05
×		117794.0013.	EPO; JPO; DERWENT; IBM TDB	10:50
!	5	(CVD or chemical adj vapor adj deposition) same plasma and 117/98.ccls.	USPAT; US-PGPUB; EPO; JPO;	2002/09/05
_	!	(CVD or chemical adj vapor adj	DERWENT;	2002/00/05
		deposition) same (si or silicon) and 117/98.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/05
- :	51	(CVD or chemical adj vapor adj deposition) same plasma same ion same beam and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/05
_	118	((CVD or chemical adj vapor adj deposition) same plasma) and 117/\$4.ccls. and ion near3 beam	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/05 17:09
_	63	((CVD or chemical adj vapor adj deposition) same plasma) same (silicon or si) and 117/\$4.ccls. and ion near3 beam	IBM_TDB   USPAT;   US-PGPUB;   EPO; JPO;	2002/09/06
-		(CVD or chemical adj vapor adj deposition) same (silicon or si) and 117/\$4.ccls. and ion near3 beam same (ar	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/09/06 10:19
L	i 	or argon)	DERWENT; IBM_TDB	

L Number	Hits	Search Text	DB	Time stamp	0 =
	76	beam same (si or silicon) same (layer or film) same ion same amorphous and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/09 16:49	. 144
-	12	CVD near3 ion same (si or silicon) and 117/\$4.ccls.	IBM_TDB USPAT; US-PGPUB;	2002/09/09 16:53	
	1		EPO; JPO; DERWENT; IBM TDB		
-	109	CVD same plasma same ion and 117/\$4.ccls.	US-PGPUB; EPO; JPO; DERWENT;	2002/09/09	
-	68	ion same (si or silicon) same (amorphous or seed or nucleus) same (beam or implant\$4) and 117/84-109.ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/10	
_	5	ion same (si or silicon) same (amorphous or seed or nucleus) same (assist\$3) and 117/84-109.ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/10	
-	17	ion same (si or silicon) same ECR and 117/\$4.ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/10	
· _	51	(si or silicon) same (ECR or "electron cyclotron resonance") and 117/\$4.ccls.	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/10	
-	19	(si or silicon) same (ECR or "electron cyclotron resonance") same ion and 117/\$4.ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/10	
-	82	ion same substrate same (beam) same amorphous and 117/\$4.ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/10	
-	14	ion same substrate same (beam) same (si or silicon) same (nucle\$4) and 117/\$4.ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/10	
-	41	ion same substrate same (si or silicon) same (nucle\$4) and 117/\$4.ccls.	IBM_TDB   USPAT;   US-PGPUB;   EPO; JPO;   DERWENT;	2002/09/10	
-	127	ion same substrate same (si or silicon) same (clean\$3 or sputter\$3) and 117/\$4.ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/10 16:54	
-	17	ion same substrate same (si or silicon) same (clean\$3 or sputter\$3) same ev and 117/\$4.ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/10 17:07	
			IBM_TDB		

, <u> </u>	,	9	ion same (si or silicon) same amorphous same ev and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/09/10 17:10
		6	CVD same plasma same ev same (si or	IBM_TDB	1 2222 /22 /22
		O	silicon) and 117/\$4.ccls.	USPAT; US-PGPUB;	2002/09/10 17:16
			1	EPO; JPO;	17.10
				DERWENT;	;
				IBM_TDB	!
-		31	CVD same plasma same (si or silicon) same	USPAT;	2002/09/10
			energy and 117/\$4.ccls.	US-PGPUB;	17:12
	!			EPO; JPO; DERWENT;	
				IBM TDB	
_		4	CVD same plasma same kev same (si or	USPAT;	2002/09/10
	1		silicon) and 117/\$4.ccls.	US-PGPUB;	17:16
				EPO; JPO;	1
				DERWENT; IBM TDB	
<b>–</b>		73	ion same (si or silicon) same amorphous	USPAT;	2002/09/11
			same energy and 117/\$4.ccls.	US-PGPUB;	09:45
		Ì		EPO; JPO;	1
				DERWENT;	1
_		83	ion same (si or silicon) same amorphous	IBM_TDB USPAT;	2002/09/11
			same beam and 117/\$4.ccls.	US-PGPUB;	10:08
		İ		EPO; JPO;	
		i		DERWENT;	
_		81	ion same (si or silicon) same	IBM_TDB	. 2002/00/11
		Ψ <u>.</u>	polycrystal\$4 same beam and 117/\$4.ccls.	USPAT; US-PGPUB;	2002/09/11 10:26
		İ	1 -1 -1 -1 -1 -1 -1 -1 -1 -1 -1 -1 -1 -1	EPO; JPO;	10.20
				DERWENT;	
		24	ion same /si or silisen\ same assistCA	IBM_TDB	2002/00/11
		Z <b>4</b>	<pre>ion same (si or silicon) same assist\$4 and 117/\$4.ccls.</pre>	USPAT; US-PGPUB;	2002/09/11 10:44
	4		22., 41.0020.	EPO; JPO;	
		1		DERWENT;	
	1	11	ml name and and and a	IBM_TDB	0000 (00 (11
		11	plasma same cvd same ion same (kev or ev) and 117/\$4.ccls.	USPAT; US-PGPUB;	2002/09/11 11:11
	1	J.		EPO; JPO;	11.11
	Ī			DERWENT;	
	ė	20		IBM_TDB	
_		38	ion near2 beam same (kev or ev) same (si or silicon) and 117/\$4.ccls.	USPAT; US-PGPUB;	2002/09/12 11:31
	,	i	of Sificon, and 117, 74. ccis.	EPO; JPO;	11.31
				DERWENT;	
				IBM_TDB	
-			ion near2 beam same (kev or ev) same sputter\$3 and 117/\$4.ccls.	USPAT;	2002/09/12
		Ť	spucceiss and 117/34.ccis.	US-PGPUB; EPO; JPO;	13:23
				DERWENT;	
		1		IBM_TDB	
_	'	32 :	100 near2 beam same mov\$4 and	USPAT;	2002/09/12
			117/\$4.ccls.	US-PGPUB; EPO; JPO;	13:37
	ı	1		DERWENT;	
	1	į		IBM TDB	
_	1		ion same mov\$4 near4 substrate and		2002/09/12
		!	117/\$4.ccls.	US-PGPUB;	14:06
	ė	1	i	EPO; JPO; : DERWENT;	
	i	1		IBM TDB	
-	į		ion near3 beam same nucle\$5 and	USPĀT;	2002/09/12
			117/\$4.ccls.		16:37
				EPO; JPO;   DERWENT;	
				IBM_TDB	

-		17 ion near3 beam same seed\$3 and	USPAT;	2002/09/12
		117/\$4.ccls.	US-PGPUB; EPO; JPO;	16:45
	ı		DERWENT;	
-		17 ion near3 beam same clean\$3 and mbe and 117/\$4.ccls.	IBM_TDB USPAT; US-PGPUB;	2002/09/12 17:06
	(1)		EPO; JPO;	17.00
	4		DERWENT;	
-	21	21 ion near3 beam same (oxide or native) and	USPAT;	2002/09/12
		mbe and 117/\$4.ccls.	US-PGPUB; EPO; JPO;	17:10
			DERWENT;	1
_	138	120 - ion - nucl-04 1 127/04	IBM_TDB	
-		138 ion same nucle\$4 and 117/\$4.ccls.	USPAT; US-PGPUB;	2002/09/13 09:22
			EPO; JPO;	05,22
	ļ		DERWENT;	
_		43 ion same substrate same (si or silicon)	IBM_TDB USPAT;	2002/09/13
	-	same beam same \$3treat\$4 and 117/\$4.ccls.	US-PGPUB;	09:50
			EPO; JPO; DERWENT;	
	1		IBM_TDB	